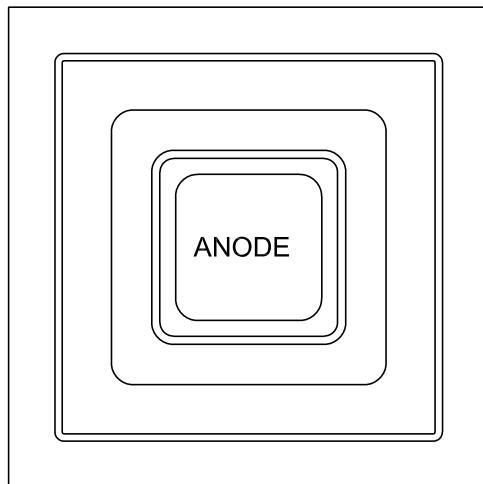


**PROCESS CPD91V**  
**Switching Diode**  
Low Leakage Switching Diode Chip

**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding pad Area	3.4 x 3.4 MILS
Top Side Metalization	Al - 15,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE: CATHODE R0

**GROSS DIE PER 4 INCH WAFER**

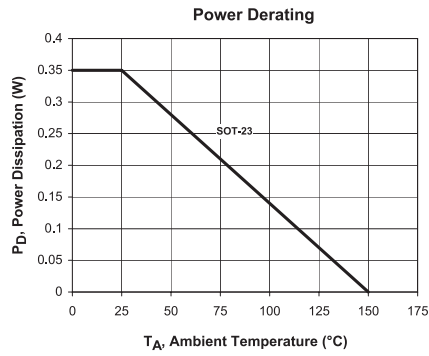
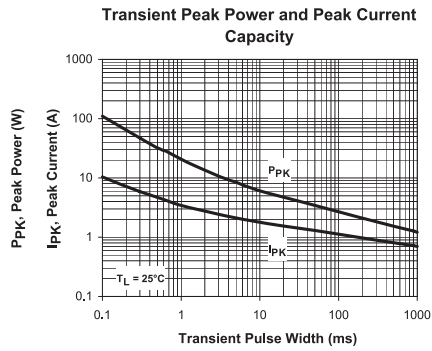
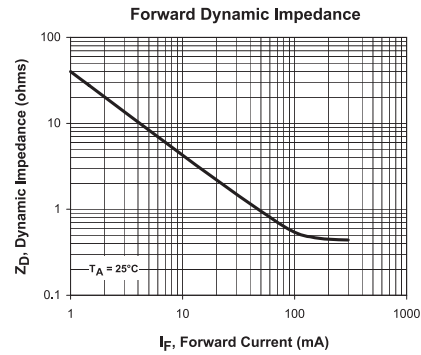
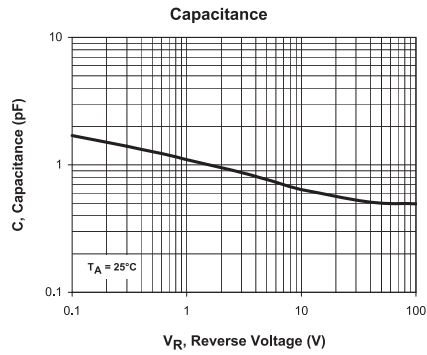
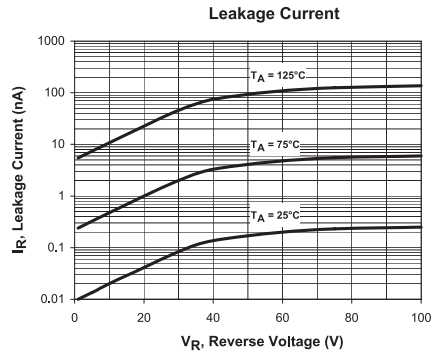
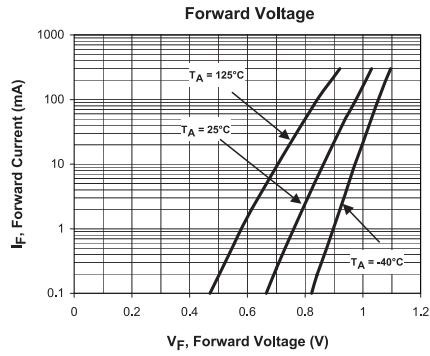
94,130

**PRINCIPAL DEVICE TYPES**

CMPD6001 Series  
CMOD6001  
CMLD6001  
CMLD6001DO  
CMDD6001

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